materials

MDPI

Supporting information

Optimization of Bilayer Resistive Random Access Memory based on Ti/HfO_2/ZrO_2/Pt

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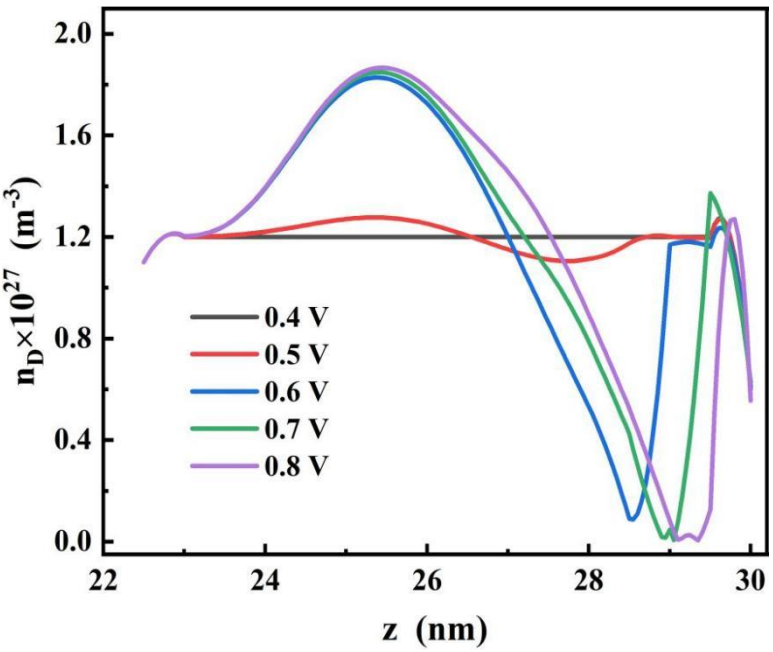

Figure S1. One−dimensional distribution curves of oxygen vacancy concentration inside CF1 and CF2 of Ti/HfO_2/ZrO_2/Pt at bias voltages 0.4 V−0.8 V (step by 0.1 V) in the SET process.

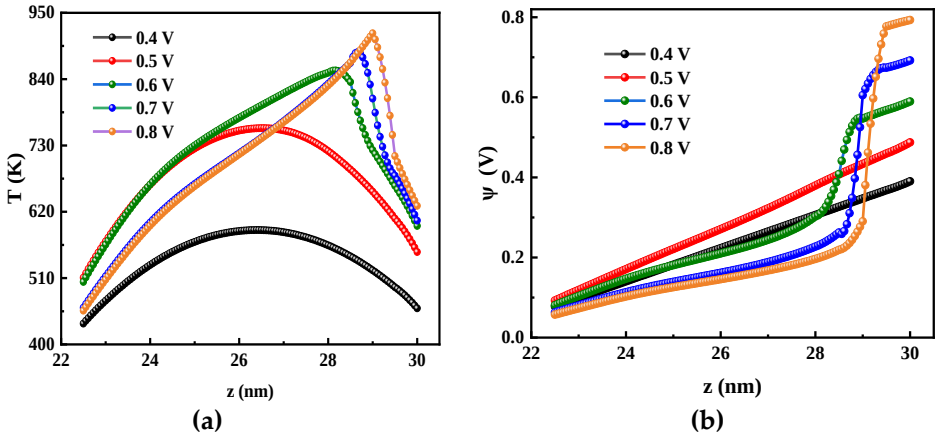

Figure S2. One−dimensional distribution curves in the SET process of Ti/HfO_2/ZrO_2/Pt at bias voltages 0.4 V- 0.8 V (step by 0.1 V): **(a)** temperature (T); **(b)** electric potential (Ψ).

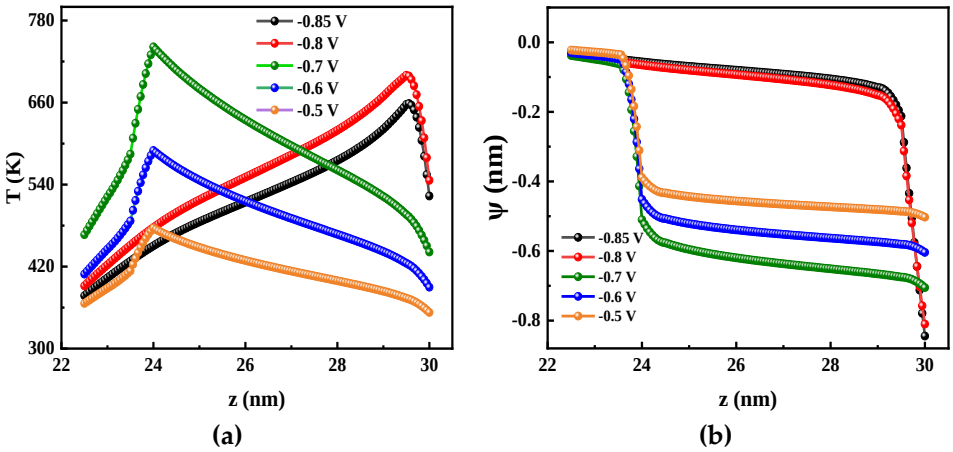

Figure S3. One−dimensional distribution curves in the SET process of Ti/HfO_2/ZrO_2/Pt at bias voltages -0.85V, -0.8V, -0.7V, -0.6V, and -0.5V: **(a)** temperature (*T*); **(b)** electric potential (*Ψ*)